





#### **N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Features**

- Extremely Low On-Resistance: 170mΩ @ V<sub>GS</sub> = 4.5V
- High Drain Current: 1.1A
- Ideal for Notebook Computer, Portable Phone, PCMCIA Cards, and Battery Powered Circuits
- ESD Protected Gate
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

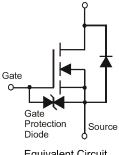
### **Mechanical Data**

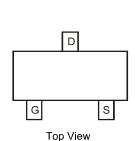
- Case: SC59
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
  Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.014 grams (approximate)

Drain









Top View Equivalent Circuit

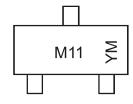
## **Ordering Information** (Note 3)

Part Number	Case	Packaging
DMN100-7-F	SC59	3000/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.

- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



M11 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

	: - J											
Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	T	U	٧	W	Х	Υ	Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage Continuous	V <sub>GSS</sub>	±20	V
Drain Current Continuous Pulsed	I <sub>D</sub>	1.1 4.0	A

# Thermal Characteristics @TA = 25°C unless otherwise specified

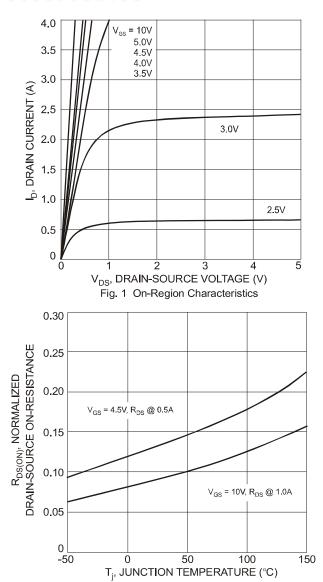
Characteristic	Symbol	Value	Units
Total Power Dissipation	$P_{D}$	500	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	250	K/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

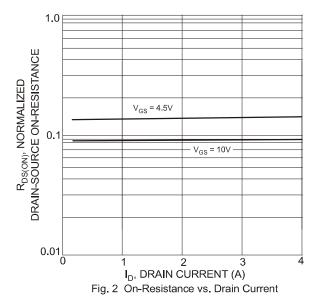
# Electrical Characteristics @TA = 25°C unless otherwise specified

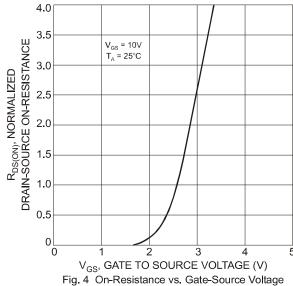
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)									
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current	@ $T_J = 25^{\circ}C$ @ $T_J = 125^{\circ}C$	I <sub>DSS</sub>	_	_	1.0 10	μА	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V		
Gate-Body Leakage		I <sub>GSS</sub>	_	_	± 100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 4)									
Gate Threshold Voltage		V <sub>GS(th)</sub>	1.0	_	3.0	V	$V_{DS} = 10V, I_{D} = 1.0mA$		
Static Drain-Source On-Resistance		R <sub>DS (ON)</sub>	_	_	0.170 0.150	Ω	$V_{GS} = 4.5V, I_D = 0.5A$ $V_{GS} = 10V, I_D = 1.0A$		
Forward Transconductance		g <sub>FS</sub>	1.3	2.4	_	S	$V_{DS} = 10V, I_{D} = 0.5A$		
DYNAMIC CHARACTERISTICS									
Input Capacitance		C <sub>iss</sub>	_	150		pF	= 10/11/10/10/10/10/10/10/10/10/10/10/10/1		
Output Capacitance		Coss	_	90	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz		
Reverse Transfer Capacitance		C <sub>rss</sub>	_	30	_	pF			
Total Gate Charge		Qg	_	5.5	_	nC	nC V <sub>DS</sub> = 24V, I <sub>D</sub> = 1,0A,		
Gate-to-Source Charge			_	8.0	_	nC	$V_{GS} = 24V, I_D = 1.0A,$ $V_{GS} = 10V$		
Gate-to-Drain Charge	Q <sub>gd</sub>	_	1.3	_	nC	VGS - 10V			
SWITCHING CHARACTERISTICS				_					
Turn-On Delay Time		t <sub>D(ON)</sub>	_	10	_	ns			
Turn-Off Delay Time		t <sub>D(OFF)</sub>	_	25		ns	$V_{DD} = 10V, I_{D} = 0.5A,$		
Turn-On Rise Time		t <sub>r</sub>	_	15	_	ns	$V_{GS}$ = 5.0V, $R_{GEN}$ = 50 $\Omega$		
Turn-Off Fall Time		t <sub>f</sub>	_	45	_	ns			
SOURCE-DRAIN RATINGS (BODY DIODE)				_					
Continuous Source Current		l <sub>S</sub>	_	_	0.54	Α	_		
Pulse Source Current		I <sub>SM</sub>	_	_	4.0	Α	_		
Forward Voltage	·	V <sub>SD</sub>	_	_	1.2	V	$I_F = 1.0A$ , $V_{GS} = 0V$		
Reverse Recovery Time		t <sub>rr</sub>		35		ns	I <sub>F</sub> = 1.0A, di/dt = 50A/μs		

Notes: 4. Pulse width  $\leq 300 \mu s,$  duty cycle  $\leq 2\%.$ 









## **Package Outline Dimensions**

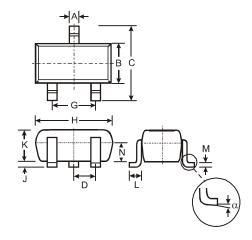
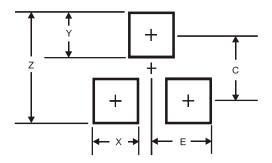


Fig. 3 On-Resistance vs. Junction Temperature

SC59							
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	-	-	0.95				
G	-	-	1.90				
H	2.90	3.10	3.00				
J	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
М	0.10	0.20	0.15				
N	0.70	0.80	0.75				
α	0°	8°	-				
All Dimensions in mm							



## Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
X	0.8
Υ	1.0
С	2.4
E	1.35

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